ABSTRACT OF THE DISCLOSURE

Provided is a plasma processing apparatus, which is loaded with a substrate to be processed on the voltage-applied electrode side and is able to achieve a uniform plasma processing characteristic on a substrate surface by correcting the distortion of an electric field in the edge portion and the distortion of plasma. There is provided a plasma processing apparatus, which introduces a processing gas into a processing chamber and excites a plasma in the processing chamber to carry out plasma processing on a substrate to be processed placed on a cathode electrode inside the processing chamber, the apparatus being provided with a ring that encompasses the outer peripheral edge portion of the substrate and has a clearance between its encompassing surface and the upper surface and the outer peripheral edge of the substrate.